



STP190NF04

STB190NF04 - STB190NF04-1

N-channel 40V - 0.0039Ω - 120A - D²PAK/I²PAK/TO-220
STripFET™ III Power MOSFET

General features

| Type | V _{DSS} | R _{DS(on)} | I _D |
|--------------|------------------|---------------------|----------------|
| STP190NF04 | 40V | <0.0043Ω | 120A |
| STB190NF04 | 40V | <0.0043Ω | 120A |
| STB190NF04-1 | 40V | <0.0043Ω | 120A |

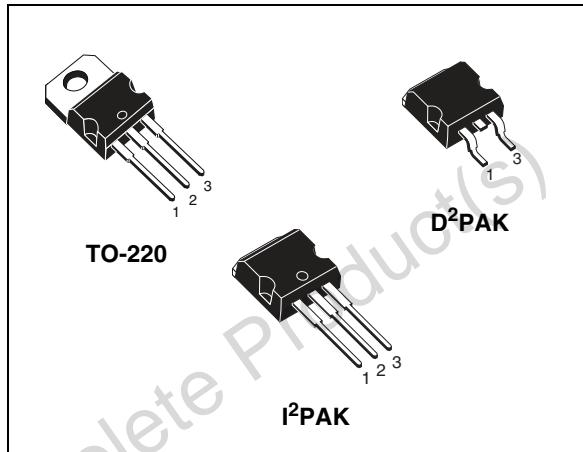
- Standard threshold drive
- 100% avalanche tested

Description

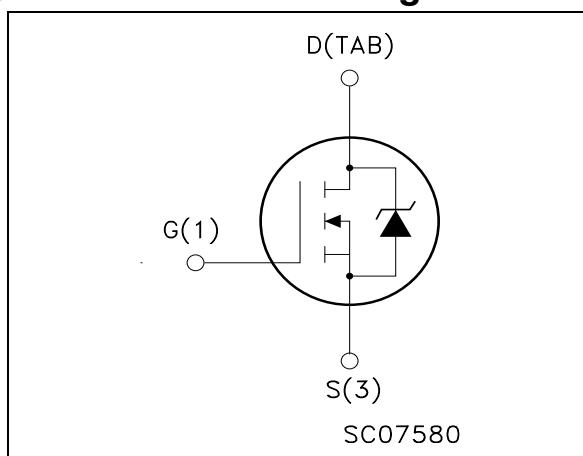
This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

Applications

- Switching application



Internal schematic diagram



Order codes

| Part number | Marking | Package | Packaging |
|--------------|----------|--------------------|-------------|
| STB190NF04T4 | B190NF04 | D ² PAK | Tape & reel |
| STB190NF04-1 | B190NF04 | I ² PAK | Tube |
| STP190NF04 | P190NF04 | TO-220 | Tube |

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1 Electrical ratings

Table 1. Absolute maximum ratings

| Symbol | Parameter | Value | Unit |
|----------------|---|------------|---------------------|
| V_{DS} | Drain-source voltage ($V_{GS} = 0$) | 40 | V |
| V_{DGR} | Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$) | 40 | V |
| V_{GS} | Gate- source voltage | ± 20 | V |
| $I_D^{(1)}$ | Drain current (continuous) at $T_C = 25^\circ\text{C}$ | 120 | A |
| $I_D^{(1)}$ | Drain current (continuous) at $T_C = 100^\circ\text{C}$ | 120 | A |
| $I_{DM}^{(2)}$ | Drain current (pulsed) | 480 | A |
| P_{tot} | Total dissipation at $T_C = 25^\circ\text{C}$ | 310 | W |
| | Derating factor | 2.07 | W/ $^\circ\text{C}$ |
| $dv/dt^{(3)}$ | Peak diode recovery voltage slope | 7 | V/ns |
| $E_{AS}^{(4)}$ | Single pulse avalanche energy | 860 | mJ |
| T_{stg} | Storage temperature | -55 to 175 | $^\circ\text{C}$ |
| T_j | Max. operating junction temperature | | |

1. Value limited by package
2. Pulse width limited by safe operating area.
3. $I_{SD} \leq 190\text{A}$, $dI/dt \leq 600\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{JMAX}$
4. Starting $T_j = 25^\circ\text{C}$, $I_D = 95\text{A}$, $V_{DD} = 35\text{V}$

Table 2. Thermal data

| | | | |
|----------------|---|------|--------------------|
| $R_{thj-case}$ | Thermal resistance junction-case max | 0.48 | $^\circ\text{C/W}$ |
| $R_{thj-amb}$ | Thermal resistance junction-ambient max | 50 | $^\circ\text{C/W}$ |
| T_J | Maximum lead temperature for soldering purpose ⁽¹⁾ | 300 | $^\circ\text{C}$ |

1. for 10 sec. 1.6mm from case

2 Electrical characteristics

($T_{CASE}=25^\circ\text{C}$ unless otherwise specified)

Table 3. On/off states

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------------|--|---|------|--------|-----------|--------------------------------|
| $V_{(BR)DSS}$ | Drain-source breakdown voltage | $I_D = 250\mu\text{A}, V_{GS} = 0$ | 40 | | | V |
| I_{DSS} | Zero gate voltage drain current ($V_{GS} = 0$) | $V_{DS} = \text{max ratings}$ $V_{DS} = \text{max ratings}, T_C = 125^\circ\text{C}$ | | | 1 10 | μA μA |
| I_{GSS} | Gate-body leakage current ($V_{DS} = 0$) | $V_{GS} = \pm 20\text{V}$ | | | ± 100 | nA |
| $V_{GS(\text{th})}$ | Gate threshold voltage | $V_{DS} = V_{GS}, I_D = 250\mu\text{A}$ | 2 | | 4 | V |
| $R_{DS(\text{on})}$ | Static drain-source on resistance | $V_{GS} = 10\text{V}, I_D = 95\text{A}$ | | 0.0039 | 0.0043 | Ω |

Table 4. Dynamic

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---|---|---|------|------------------------|------|----------------------|
| $g_{fs}^{(1)}$ | Forward transconductance | $V_{DS} = 15\text{V}, I_D = 95\text{A}$ | | 200 | | s |
| C_{iss} C_{oss} C_{rss} | Input capacitance Output capacitance Reverse transfer capacitance | $V_{DS} = 25\text{V}, f = 1\text{MHz}, V_{GS} = 0$ | | 5800 1500 200 | | pF pF pF |
| $t_{d(on)}$ t_r $t_{d(off)}$ t_f | Turn-on delay time Rise time Turn-off delay time Fall time | $V_{DD} = 20\text{V}, I_D = 95\text{A}$ $R_G = 4.7\Omega, V_{GS} = 10\text{V}$ (see Figure 15) | | 45 380 100 75 | | ns ns ns ns |
| Q_g Q_{gs} Q_{gd} | Total gate charge Gate-source charge Gate-drain charge | $V_{DD} = 20\text{V}, I_D = 190\text{A}, V_{GS} = 5\text{V}$ (see Figure 16) | | 130 40 45 | | nC nC nC |

1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

Table 5. Source drain diode

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------------------------------|--|--|------|------------------|------------|---------------|
| I_{SD} $I_{SDM}^{(1)}$ | Source-drain current Source-drain current (pulsed) | | | | 120 480 | A A |
| $V_{SD}^{(2)}$ | Forward on voltage | $I_{SD} = 120\text{A}$, $V_{GS} = 0$ | | | 1.3 | V |
| t_{rr} Q_{rr} I_{RRM} | Reverse recovery time Reverse recovery charge Reverse recovery current | $I_{SD} = 190\text{A}$, $dI/dt = 100\text{A}/\mu\text{s}$, $V_{DD} = 34\text{V}$, $T_j = 150^\circ\text{C}$ (see Figure 17) | | 90 295 6.5 | | ns nC A |

1. Pulse width limited by safe operating area.
 2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

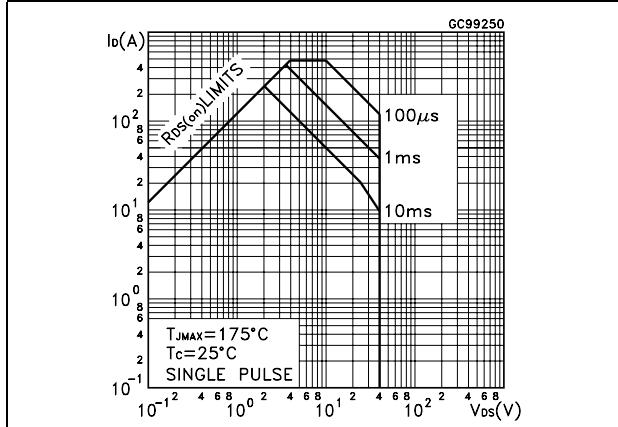


Figure 2. Thermal impedance

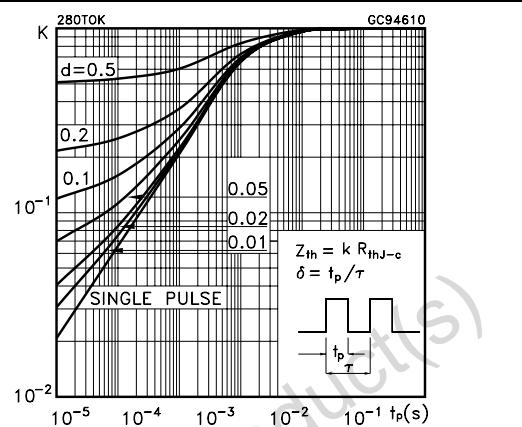


Figure 3. Output characteristics

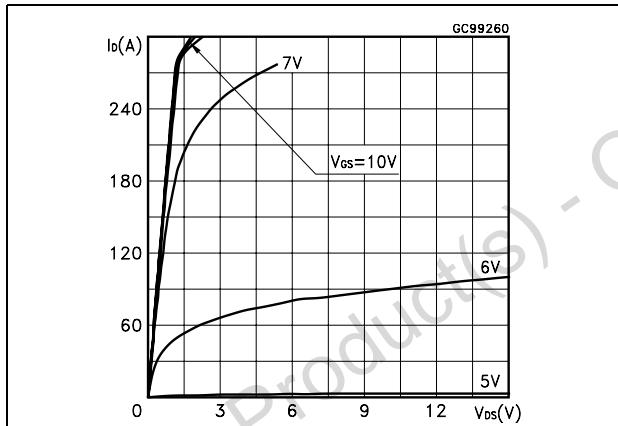


Figure 4. Transfer characteristics

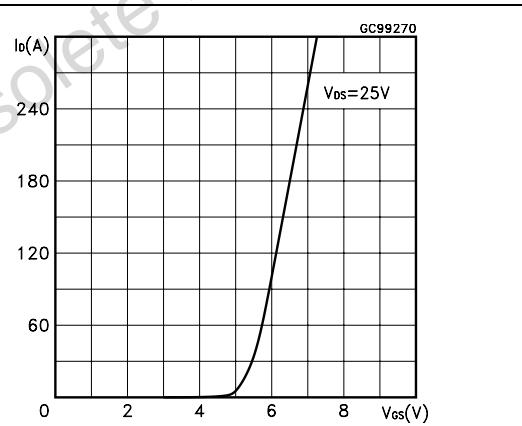


Figure 5. Transconductance

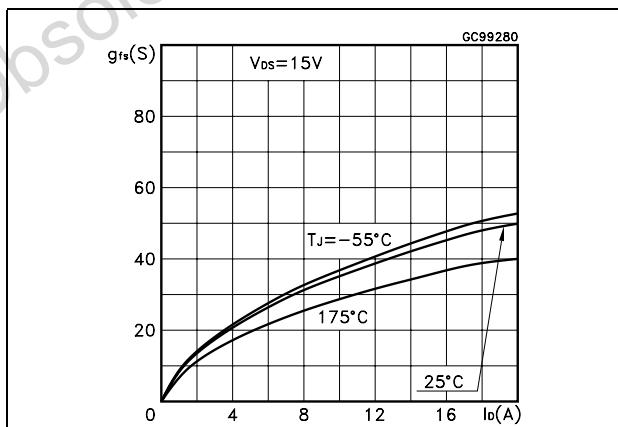


Figure 6. Static drain-source on resistance

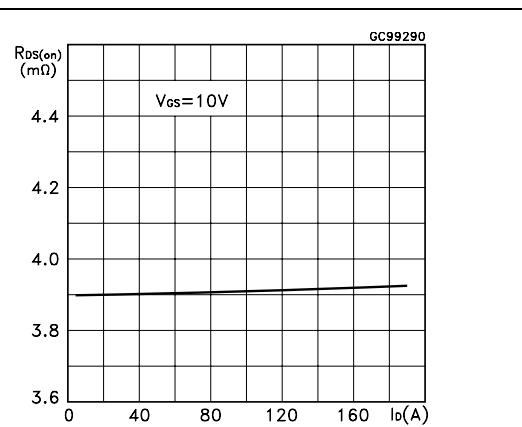


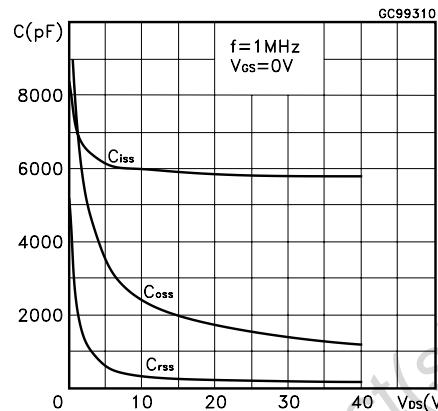
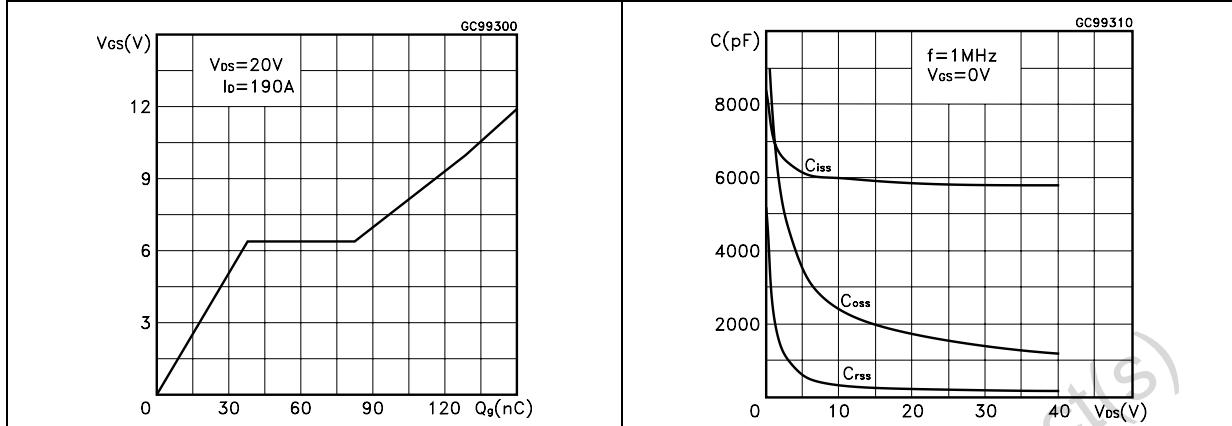
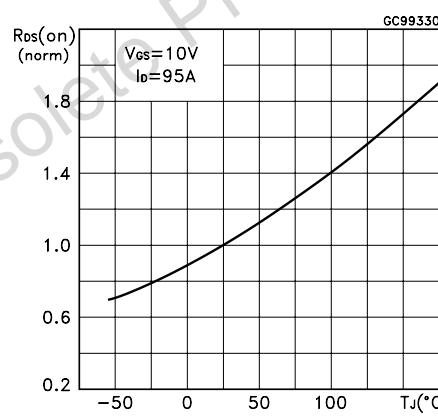
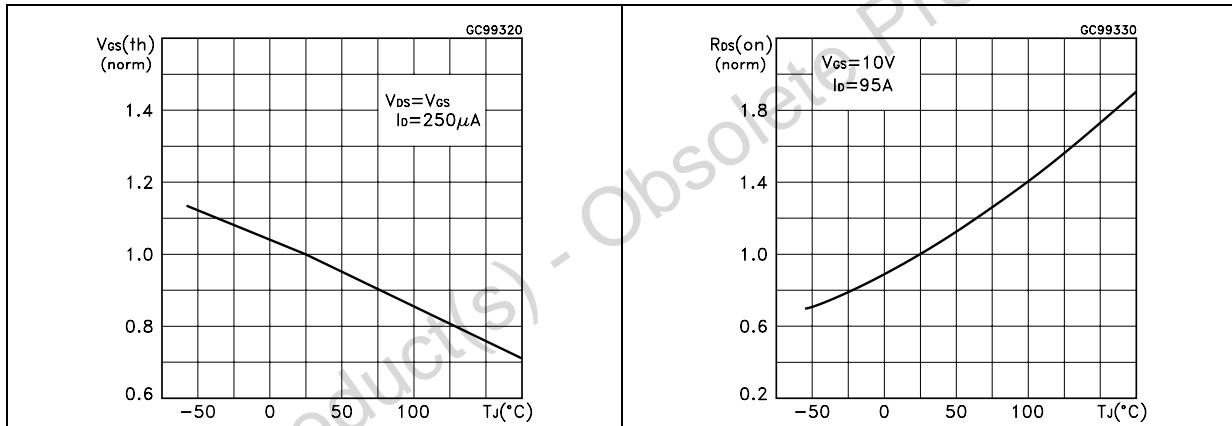
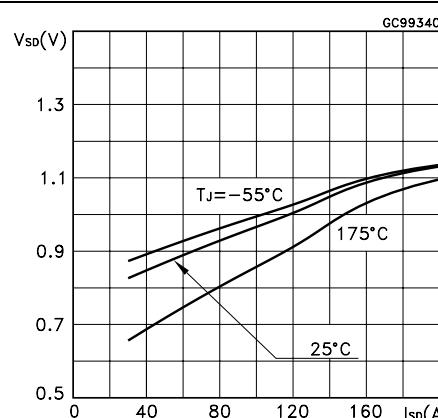
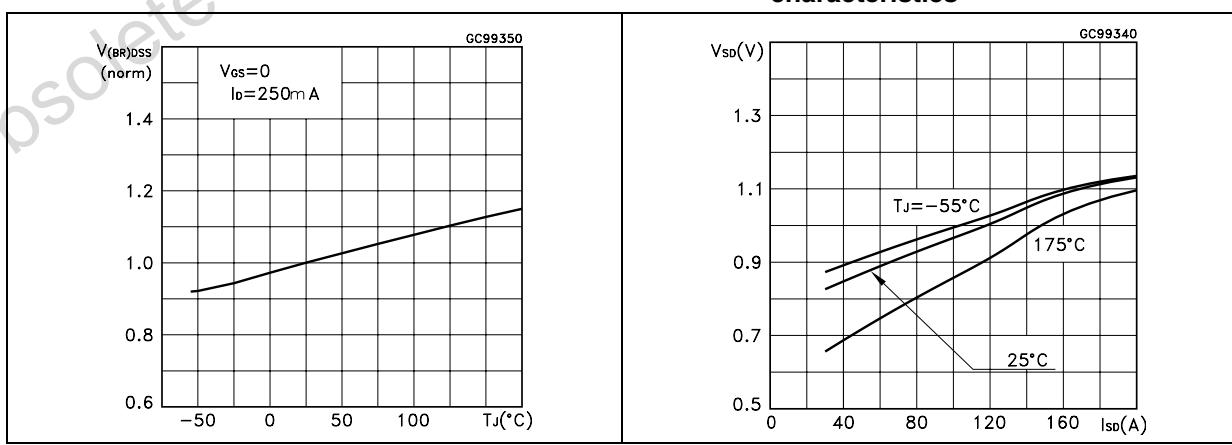
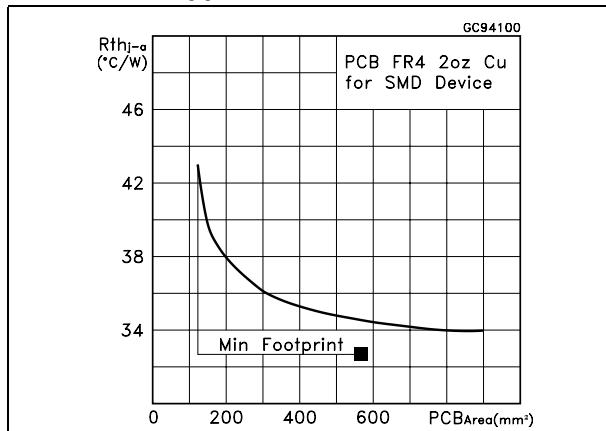
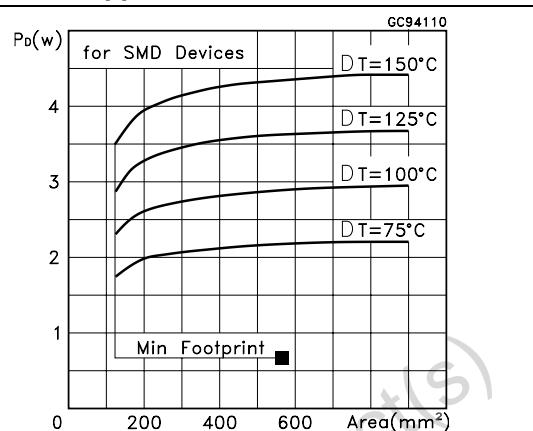
Figure 7. Gate charge vs gate-source voltage **Figure 8.** Capacitance variations**Figure 9.** Normalized gate threshold voltage vs temperature**Figure 10.** Normalized on resistance vs temperature**Figure 11.** Normalized B_{VDSS} vs temperature**Figure 12.** Source-drain diode forward characteristics

Figure 13. Thermal resistance r_{thj-a} vs PCB copper area**Figure 14. Max power dissipation vs PCB copper area**

3 Test circuit

Figure 15. Switching times test circuit for resistive load

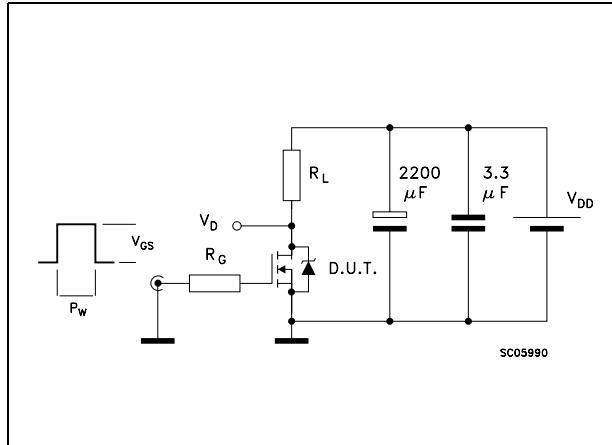


Figure 17. Test circuit for inductive load switching and diode recovery times

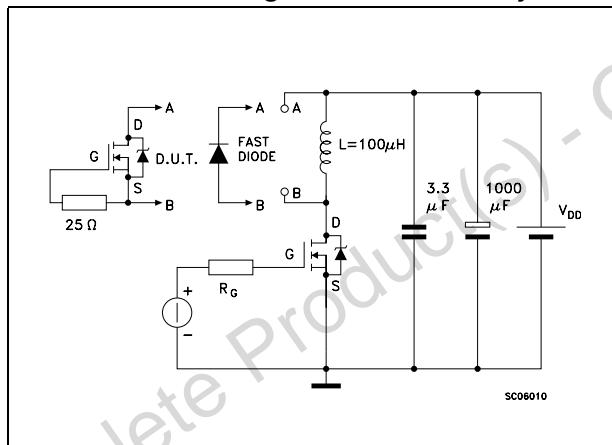


Figure 16. Gate charge test circuit

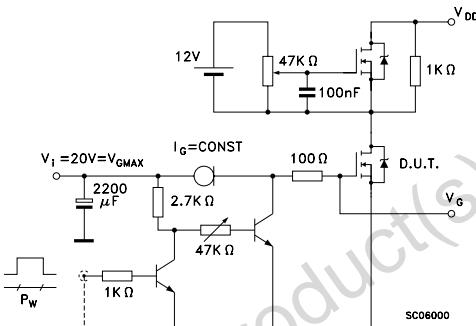


Figure 18. Unclamped Inductive load test circuit

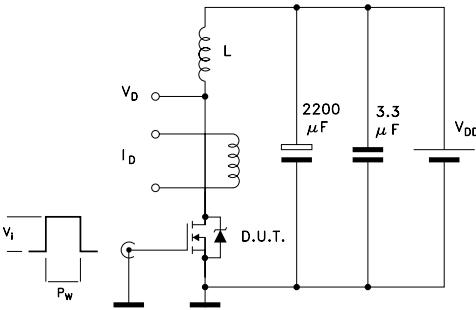


Figure 19. Unclamped inductive waveform

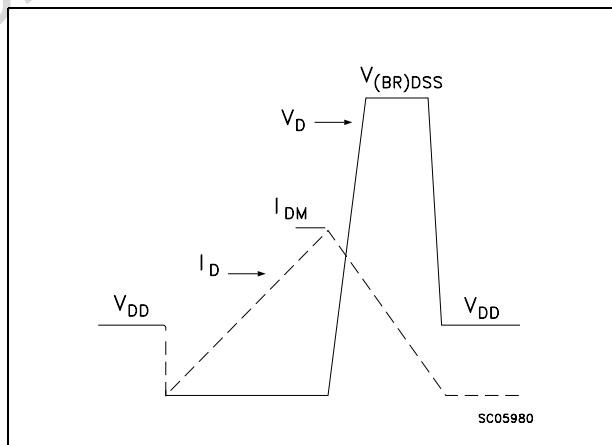
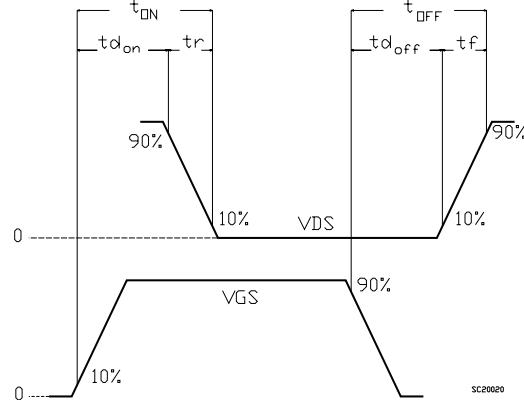


Figure 20. Switching time waveform

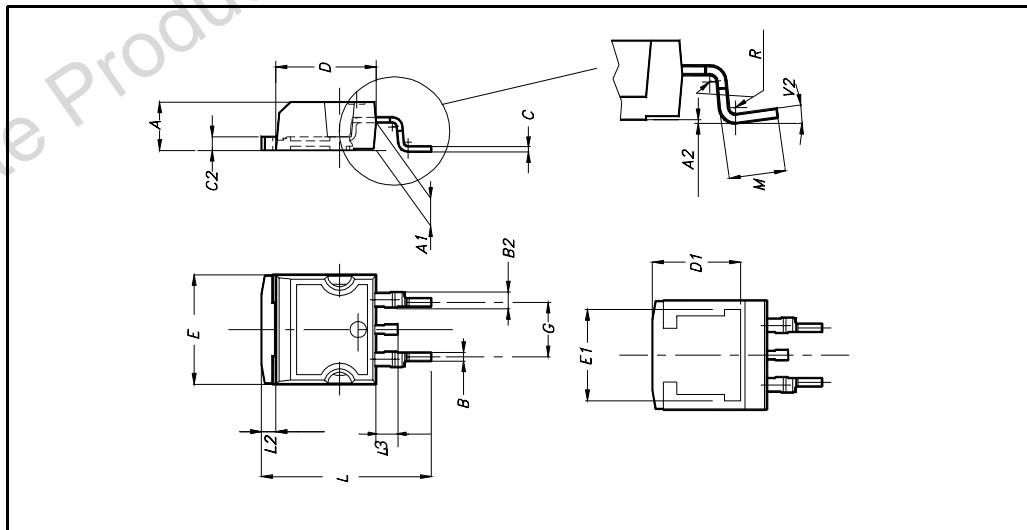


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

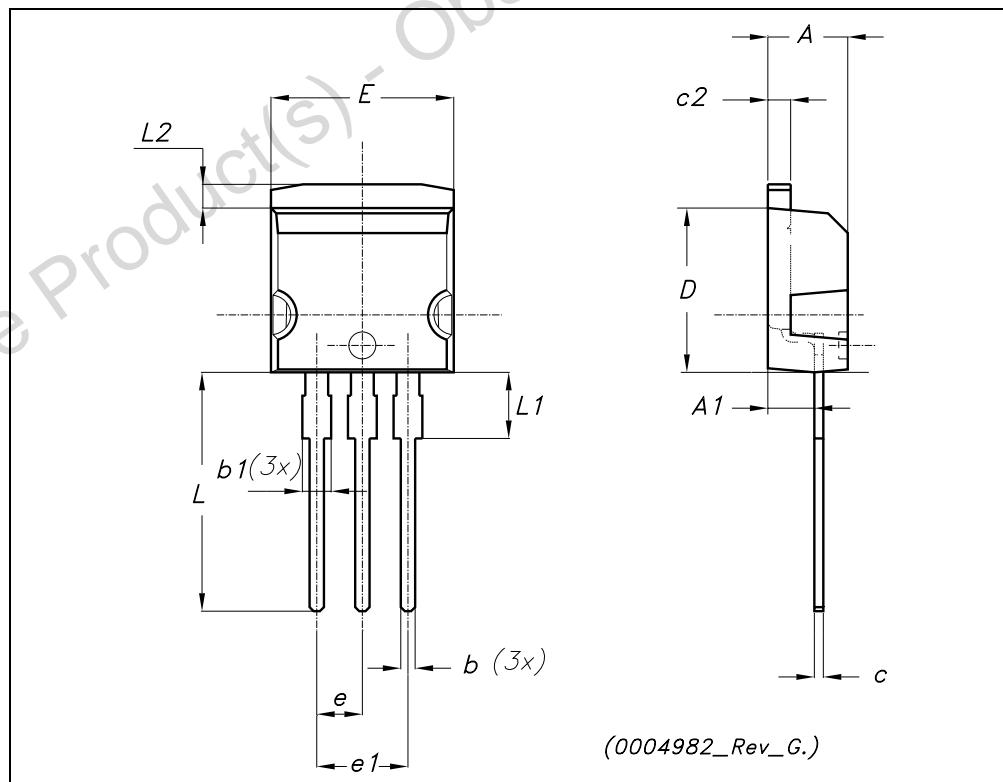
D²PAK MECHANICAL DATA

| DIM. | mm. | | | inch | | |
|------|------|------|-------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 4.4 | | 4.6 | 0.173 | | 0.181 |
| A1 | 2.49 | | 2.69 | 0.098 | | 0.106 |
| A2 | 0.03 | | 0.23 | 0.001 | | 0.009 |
| B | 0.7 | | 0.93 | 0.027 | | 0.036 |
| B2 | 1.14 | | 1.7 | 0.044 | | 0.067 |
| C | 0.45 | | 0.6 | 0.017 | | 0.023 |
| C2 | 1.23 | | 1.36 | 0.048 | | 0.053 |
| D | 8.95 | | 9.35 | 0.352 | | 0.368 |
| D1 | | 8 | | | 0.315 | |
| E | 10 | | 10.4 | 0.393 | | |
| E1 | | 8.5 | | | 0.334 | |
| G | 4.88 | | 5.28 | 0.192 | | 0.208 |
| L | 15 | | 15.85 | 0.590 | | 0.625 |
| L2 | 1.27 | | 1.4 | 0.050 | | 0.055 |
| L3 | 1.4 | | 1.75 | 0.055 | | 0.068 |
| M | 2.4 | | 3.2 | 0.094 | | 0.126 |
| R | | 0.4 | | | 0.015 | |
| V2 | 0° | | 4° | | | |



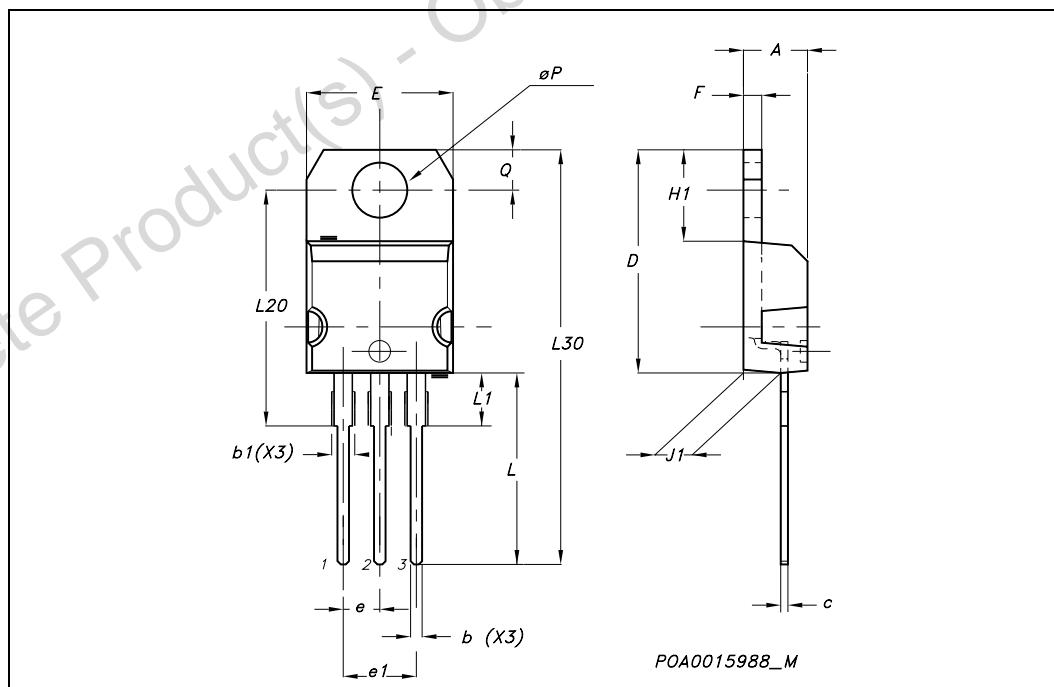
TO-262 (I²PAK) MECHANICAL DATA

| DIM. | mm. | | | inch | | |
|------|------|------|-------|-------|------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 4.40 | | 4.60 | 0.173 | | 0.181 |
| A1 | 2.40 | | 2.72 | 0.094 | | 0.107 |
| b | 0.61 | | 0.88 | 0.024 | | 0.034 |
| b1 | 1.14 | | 1.70 | 0.044 | | 0.066 |
| c | 0.49 | | 0.70 | 0.019 | | 0.027 |
| c2 | 1.23 | | 1.32 | 0.048 | | 0.052 |
| D | 8.95 | | 9.35 | 0.352 | | 0.368 |
| e | 2.40 | | 2.70 | 0.094 | | 0.106 |
| e1 | 4.95 | | 5.15 | 0.194 | | 0.202 |
| E | 10 | | 10.40 | 0.393 | | 0.410 |
| L | 13 | | 14 | 0.511 | | 0.551 |
| L1 | 3.50 | | 3.93 | 0.137 | | 0.154 |
| L2 | 1.27 | | 1.40 | 0.050 | | 0.055 |

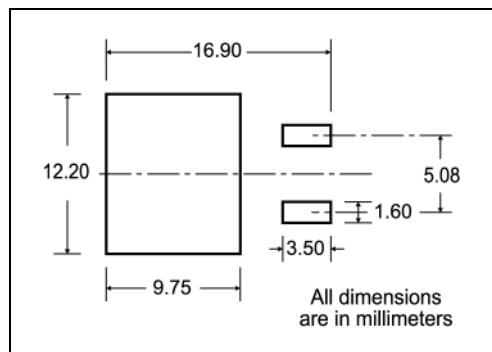
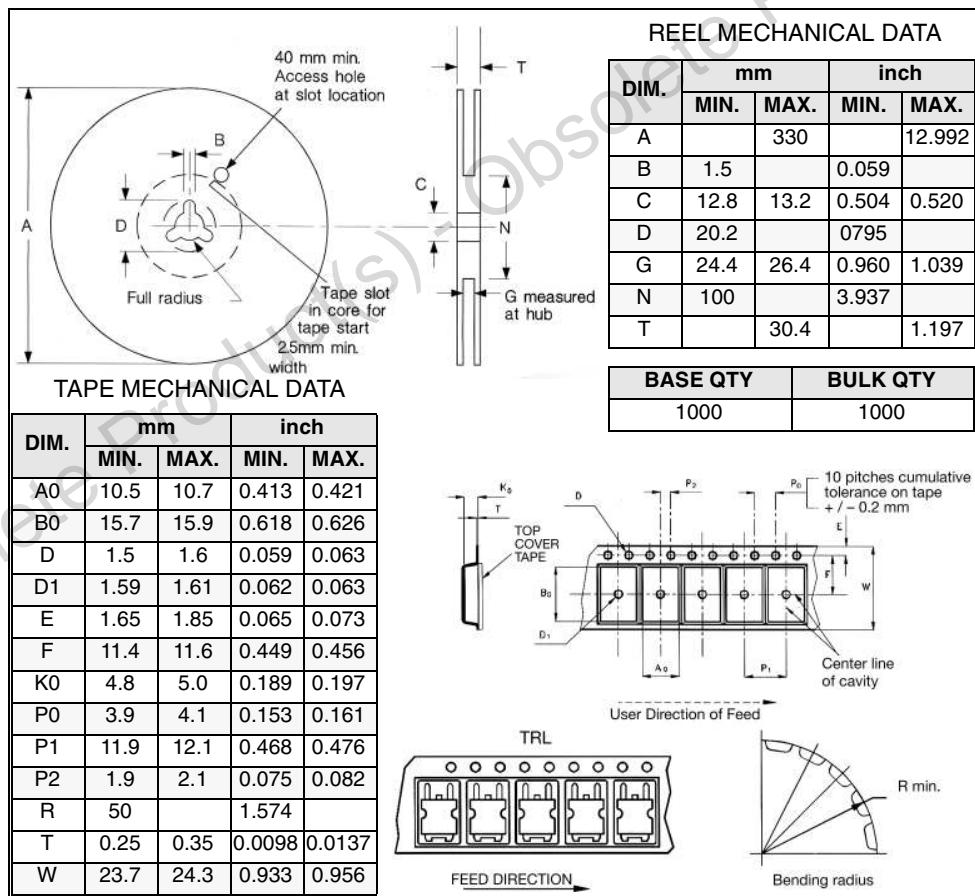


TO-220 MECHANICAL DATA

| DIM. | mm. | | | inch | | |
|------|-------|-------|-------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 4.40 | | 4.60 | 0.173 | | 0.181 |
| b | 0.61 | | 0.88 | 0.024 | | 0.034 |
| b1 | 1.15 | | 1.70 | 0.045 | | 0.066 |
| c | 0.49 | | 0.70 | 0.019 | | 0.027 |
| D | 15.25 | | 15.75 | 0.60 | | 0.620 |
| E | 10 | | 10.40 | 0.393 | | 0.409 |
| e | 2.40 | | 2.70 | 0.094 | | 0.106 |
| e1 | 4.95 | | 5.15 | 0.194 | | 0.202 |
| F | 1.23 | | 1.32 | 0.048 | | 0.052 |
| H1 | 6.20 | | 6.60 | 0.244 | | 0.256 |
| J1 | 2.40 | | 2.72 | 0.094 | | 0.107 |
| L | 13 | | 14 | 0.511 | | 0.551 |
| L1 | 3.50 | | 3.93 | 0.137 | | 0.154 |
| L20 | | 16.40 | | | 0.645 | |
| L30 | | 28.90 | | | 1.137 | |
| øP | 3.75 | | 3.85 | 0.147 | | 0.151 |
| Q | 2.65 | | 2.95 | 0.104 | | 0.116 |



5 Packaging mechanical data

D²PAK FOOTPRINT**TAPE AND REEL SHIPMENT**

6 Revision history

Table 6. Revision history

| Date | Revision | Changes |
|-------------|----------|---------------------------------|
| 09-Sep-2004 | 1 | First version |
| 09-Aug-2006 | 2 | New template, no content change |

Obsolete Product(s) - Obsolete Product(s)

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